

ROITHNER LASERTECHNIK

A-1040 WIEN, FLEISCHMANNGASSE 9

TEL: +43 -1- 586 52 43 FAX: +43 -1- 586 41 43

e-mail: office@roithner-laser.com http://www.roithner-laser.com

RLT7850MG

TECHNICAL DATA



High Power Infrared Laserdiode

Structure: **AlGaAs**, index guided, single transverse mode

Lasing wavelength: **785 nm typ.**

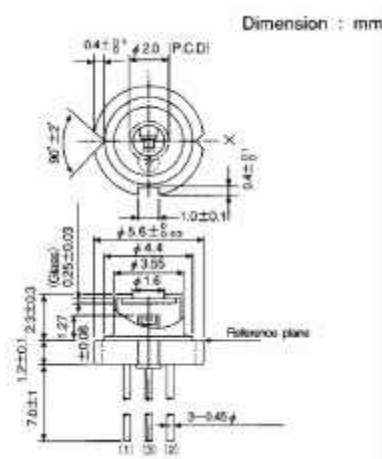
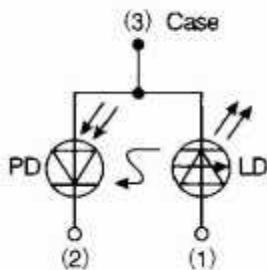
Max. optical power: **50 mW cw**

Package: **5.6 mm**



NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:



Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power cw	P_o	60	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	30	V
Operation Case Temperature	T_c	-10 .. +60	°C
Storage Temperature	T_{STG}	-10 .. +100	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P_o	kink free		50	70 *)	mW
Threshold Current	I_{th}	cw		55	80	mA
Operation Current	I_{op}	$P_o = 50$ mW		140	165	mA
Operating Voltage	V_{op}	$P_o = 50$ mW		2.0	2.5	V
Lasing Wavelength	λ_p	$P_o = 50$ mW	770	785	800	nm
Beam Divergence	$\theta_{//}$	$P_o = 50$ mW	8	10	13	°
Beam Divergence	$\theta_{\perp}$	$P_o = 50$ mW	22	25	28	°
Slope efficiency	η	$P_o = 50$ mW	0.40	0.55	0.75	mW/mA
Monitor Current	I_m	$P_o = 50$ mW, $V_f = 5$ V		0.2	0.4	mA

*) Note: Duty cycle less than 50%, pulse width less than 1μs